

1201.63407

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nayfeh et al.

Serial No.: 09/496,506

Filed: February 2, 2000

For: SILICON NANOPARTICLE FIELD
EFFECT TRANSISTOR AND
TRANSISTOR MEMORY DEVICE

Group Art Unit:

#4/a
6/29/00
Jurel
I hereby certify that this paper is being deposited with
the United States Postal Service as first-class mail in
an envelope addressed to: Assistant Commissioner for
Patents, Washington, D.C. 20231, on this date.

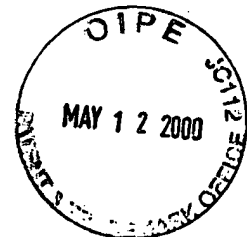
5/9/00

Date
F-CLASS.WCM

Registration No. 35132
Attorney for Applicant

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

Prior to examination of this application, please amend the application as
follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 9, line 12, delete "particles of 1 nm across contain less than one in a
million holes," and insert /less than one in one million particles may contain a hole,/.
M